

## MBD4448W SWITCHING DIODE

### FEATURES

Power dissipation

$P_D$ : 200 mW ( $T_{amb}=25^\circ\text{C}$ )

Collector current

$I_O$ : 250 mA

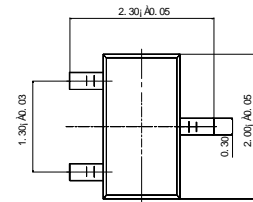
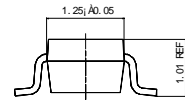
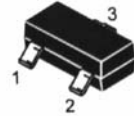
Collector-base voltage

$V_R$ : 75 V

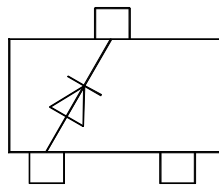
Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$

### SOT-323



Unit: mm



Marking: KA3

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=10\mu\text{A}$	75		V
Reverse voltage leakage current	$I_R$	$V_R=20\text{V}$ $V_R=75\text{V}$		0.025 2.5	$\mu\text{A}$
Forward voltage	$V_F$	$I_F=5\text{mA}$ $I_F=10\text{mA}$ $I_F=100\text{mA}$ $I_F=150\text{mA}$		0.72 0.855 1 1.25	V
Diode capacitance	$C_D$	$V_R=0\text{V}, f=1\text{MHz}$		4	pF
Reverse recovery time	$t_{rr}$	$I_F=I_R=10\text{mA}$ $I_{rr}=0.1 \times I_R, R_L=100\Omega$		4	nS

Test period  $<3000\mu\text{s}$ .